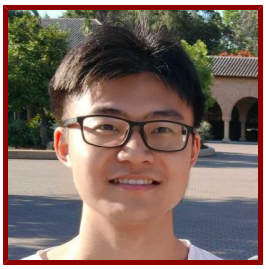
Stanford



Xiangjin Wu

- Ph.D. Student in Electrical Engineering, admitted Autumn 2021
- Masters Student in Electrical Engineering, admitted Spring 2024

Bio

BIO

Xiangjin Wu is a Ph.D. candidate in the Department of Electrical Engineering at Stanford University, co-advised by Prof. Eric Pop and Prof. H.-S. Philip Wong. He received his B.S. in Physics with Honors from Nanjing University in 2020. His research focuses on novel materials and heterostructures for memory applications, including phase change memory (PCM), dynamic random-access memory (DRAM), and their interconnects. Xiangjin is a recipient of the Samsung fellowship.

HONORS AND AWARDS

- Samsung Fellowship, Samsung (September, 2023)
- Best Poster Award, Non-Volatile Memory Technology Symposium (NVMTS) (December, 2022)

EDUCATION AND CERTIFICATIONS

- B.S., Nanjing University , Physics (2020)

LINKS

- Google Scholar: https://scholar.google.com/citations?user=VyA8OUYAAAAJ&hl=en
- http://poplab.stanford.edu/: http://poplab.stanford.edu/
- https://nano.stanford.edu/: https://nano.stanford.edu/

Publications

PUBLICATIONS

- **Novel nanocomposite-superlattices for low energy and high stability nanoscale phase-change memory.** *Nature communications*
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- **Understanding Interface-Controlled Resistance Drift in Superlattice Phase Change Memory** *IEEE ELECTRON DEVICE LETTERS*
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- **Unveiling the Effect of Superlattice Interfaces and Intermixing on Phase Change Memory Performance.** *Nano letters*
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- **Multiple Tunable Hyperbolic Resonances in Broadband Infrared Carbon-Nanotube Metamaterials** *PHYSICAL REVIEW APPLIED*
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- **Uniform and ultrathin high-kappa gate dielectrics for two-dimensional electronic devices** *NATURE ELECTRONICS*
  Li, W., Zhou, J., Cai, S., Yu, Z., Zhang, J., Fang, N., Li, T., Wu, Y., Chen, T., Xie, X., Ma, H., Yan, K., Dai, et al
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